Dual Bias Resistor Transistor

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

IMD10AMT1G

- High Current: I_C = 500 mA max
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	5.0	Vdc
Collector Current - Continuous	I _C	500	mAdc

THERMAL CHARACTERISTICS

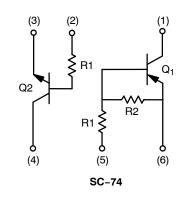
Characteristic	Symbol	Max	Unit
Power Dissipation*	P_{D}	285	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAM



SC-74R 318AA Style 21



D10 = Specific Device Code

= Date Code

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
IMD10AMT1G	SC-74R (Pb-Free)	3000 / Tape & Reel
NSVIMD10AMT1G	SC-74R (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Total for both Transistors.

IMD10AMT1G

ELECTRICAL CHARACTERISTICS

(T_A = 25 $^{\circ}\text{C}$ unless otherwise noted, common for Q_1 and Q_2, – minus sign for Q_1(PNP) omitted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Base Breakdown Voltage ($I_C = 50 \mu Adc, I_E = 0 A$)	V _(BR) CBO	50	-	Vdc
Collector–Emitter Breakdown Voltage (I _C = 1.0 mAdc, I _B = 0 A)	V _(BR) CEO	50	-	Vdc
Emitter-Base Breakdown Voltage (I _E = 50 μAdc, I _C = 0 A)	V _{(BR)EBO}	5.0	-	Vdc
Collector-Base Cutoff Current (V _{CB} = 50 Vdc, I _E = 0 A)	I _{CBO}	-	100	nA
Emitter-Base Cutoff Current Q1 (PNP) $(V_{EB} = 6.0 \text{ Vdc}, I_{C} = 0 \text{ A})$ Q2 (NPN)	I _{EBO}	- -	1.0 0.5	mA
Collector-Emitter Cutoff Current (V _{CE} = 25 Vdc, I _B = 0 A)	I _{CES}	-	100	nA
ON CHARACTERISTICS (Note 1)				
DC Current Gain $ (V_{CE} = 5.0 \text{ V, I}_{C} = 100 \text{ mA}) \text{ Q1(PNP)} $	h _{FE}	68 100	_ 600	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	-	0.3	Vdc
Output Voltage (on) $(V_{CC}=5.0 \text{ V}, V_B=2.5 \text{ V}, R_L=1.0 \text{ k}\Omega)$	V _{OL}	-	0.2	Vdc
Output Voltage (off) $(V_{CC}=5.0 \text{ V}, V_B=0.25 \text{ V}, R_L=1.0 \text{ k}\Omega)$	V _{OH}	4.9	-	Vdc
Input Resistor Q1(PNP) Q2(NPN)	R1	70 7.0	130 13	Ω kΩ
Resistor Ratio Q1(PNP) Q2(NPN)	R1/R2	0.008	0.012 -	

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle < 2.0%.

IMD10AMT1G

TYPICAL CHARACTERISTICS (NPN)

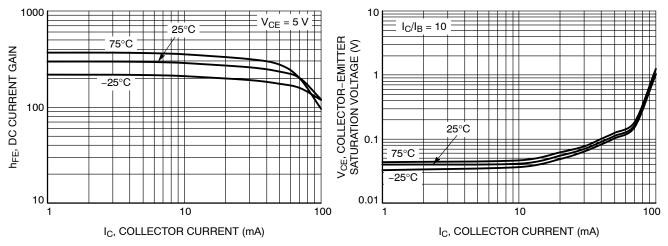


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

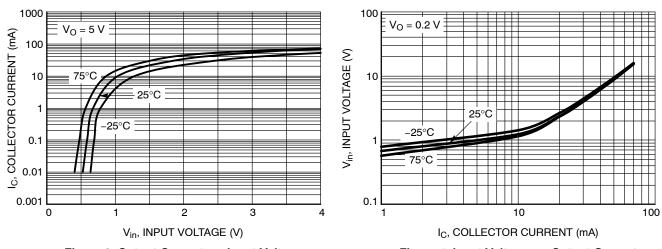


Figure 3. Output Current vs. Input Voltage

Figure 4. Input Voltage vs. Output Current

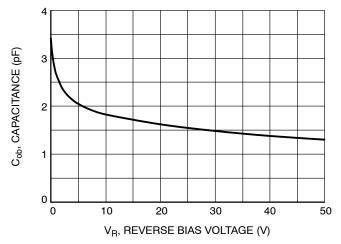


Figure 5. Output Capacitance

IMD10AMT1G

TYPICAL CHARACTERISTICS (PNP)

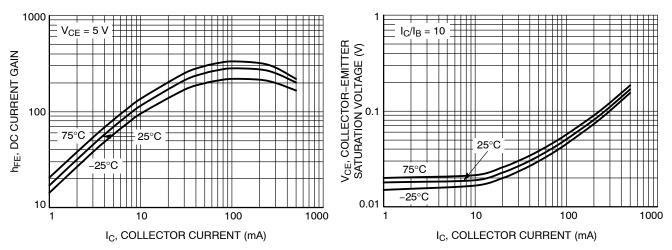


Figure 6. DC Current Gain

Figure 7. Collector-Emitter Saturation Voltage

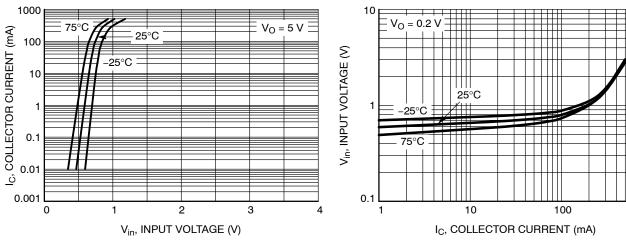


Figure 8. Output Current vs. Input Voltage

Figure 9. Input Voltage vs. Output Current

1000

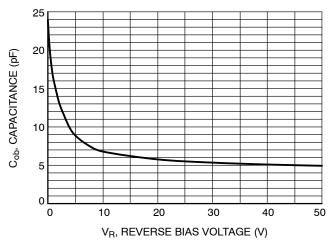


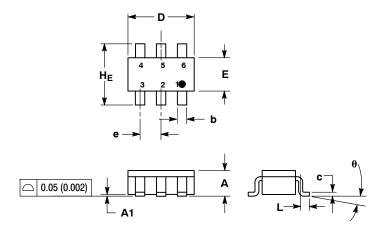
Figure 10. Output Capacitance





SC-74R CASE 318AA-01 **ISSUE B**

DATE 27 MAY 2005



- NOTES:

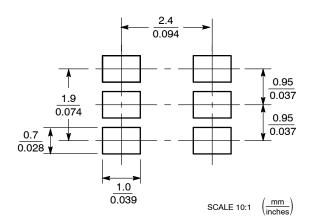
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM*

GENERIC



XXX= Specific Device Code = Date Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 20:	STYLE 21:
PIN 1. COLLECTOR 1	PIN 1. COLLECTOR 1
2. BASE 2	2. EMITTER 2
EMITTER 2	3. BASE 2
COLLECTOR 2	4. COLLECTOR 2
5. BASE 1	EMITTER 1
EMITTER 1	6. BASE 1

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